

Amendments to the Specification

Please replace the paragraph [0038] at page 10, lines 3-6 with the following amended paragraph:

[0038] FIGS. 4a-4c show how the semiconductor device depicted in FIG. 1a can be intentionally turned ON by the present invention to give the appearance of a functioning transistor device to the reverse engineer when in fact the transistor is never turned ~~tamed~~ OFF. The processing steps preferably utilized to arrive at the device shown in FIG. 4c will be discussed subsequently.

Please replace the paragraph [0056] at page 18, lines 8-25 with the following amended paragraph:

[0056] It is very difficult for the reverse engineer to detect the techniques disclosed herein. For example, even when using microscopic investigations ~~investigates~~ like SEM analysis on the top (plan view) side of the circuit of semiconductor devices altered by the techniques herein disclosed, the altered circuit will look identical to other standard semiconductor devices. Should the reverse engineer determine that further analysis of all millions of the semiconductor devices is required, then the metal, oxide, and insulation layers must be carefully removed. Next, the reverse engineer must perform a stain and etch to determine that the well implant has been placed where the gate had been. This will be difficult because for many dense ICs there will always be a well implant under the gate, only the well implant is usually a different type than the active regions adjacent to the gate region. However, in the case of the present invention, the well will be the same type as the semiconductor active regions adjacent to the gate region. Therefore, the reverse engineer must be able to determine between the different types of well conductivity types. Using the present techniques, the gate well implants are low dose. Thus, the chemical etches dependent on the chemical nature of the implanted material will not be as effective. As a result, it is believed that the techniques which will be needed to detect the use of the present invention will be sufficiently time consuming to deter the reverse engineer. A complex integrated circuit may comprise

millions of semiconductor devices, and if the reverse engineer must carefully analyze each semiconductor device in order to determine whether or not the present invention has been used to disguise each semiconductor device, the effort involved in reverse engineering such an integrated circuit will be tremendous.